TECH PUBLIC
台舟电子

TPB01A30-0201
Schottky barrier diode

www.sot23.com.tw

Features

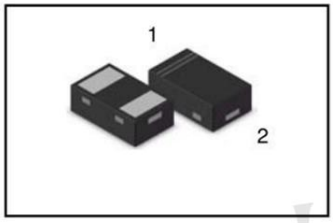
- Average forward current: $I_{F(AV)}$ 100 mA
- Reverse voltage: V_R 30 V
- Low forward voltage: V_F 500 mV @10mA
- Low reverse current: I_R 0.7μ A
- Leadless ultra small SMD plastic package
- We declare that the material of product compliance with RoHS requirements and Halogen Free

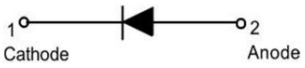
Applications

- Low current rectification

RoHS

DFN0603(0201)





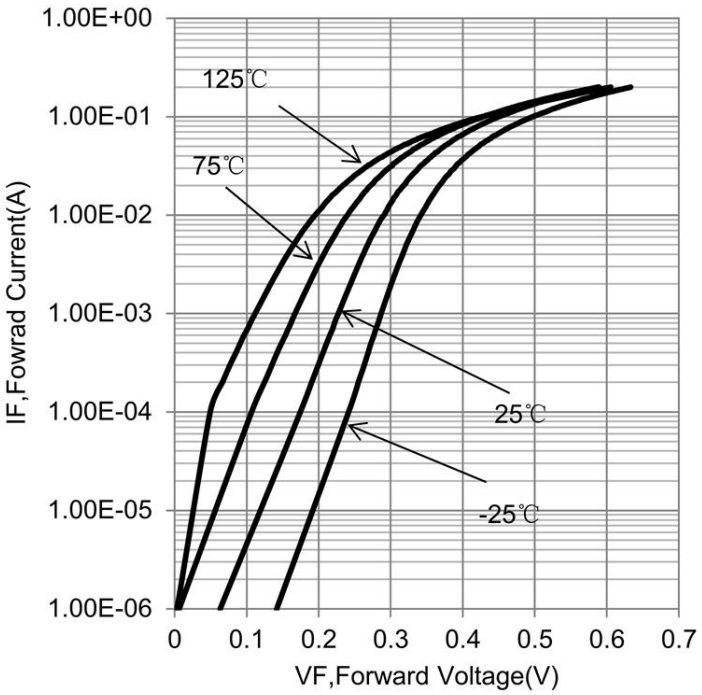
Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Limits	Unit
Reverse voltage(DC)	V_R	30	V
Peak forward current	I_{FM}	200	mA
Average rectified forward current	Io	100	mA
Peak forward surge current	I_{FSM}	2	A
Junction temperature	T_j	125	℃
Storage Temperature Range	T_{STG}	-40~+125	℃

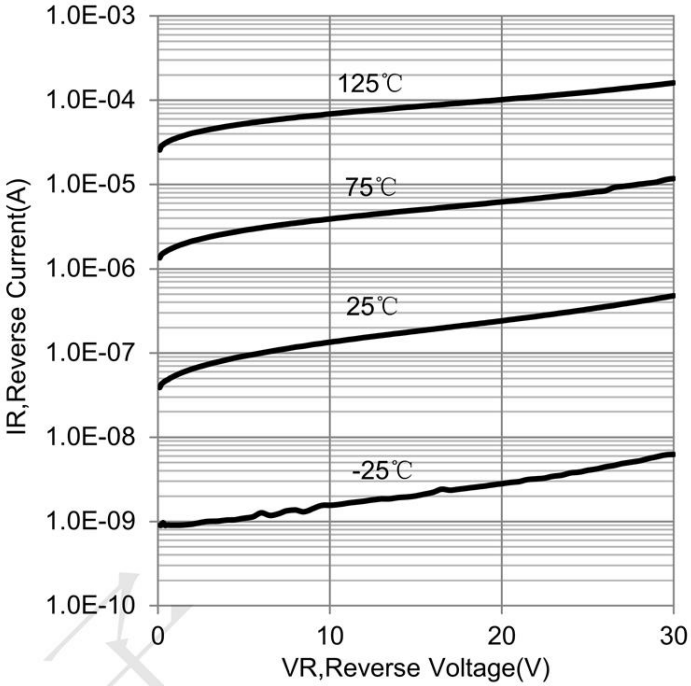
Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.38	0.5	V	I_F=10mA
		-	0.53	0.6	V	I_F=100 mA
Reverse current	I_R			0.35	μA	V_R=10V
		-		0.7	μA	V_R=30V
Total capacitance	C_t	-	8		pF	V_R = 0 V, f = 1 MHz

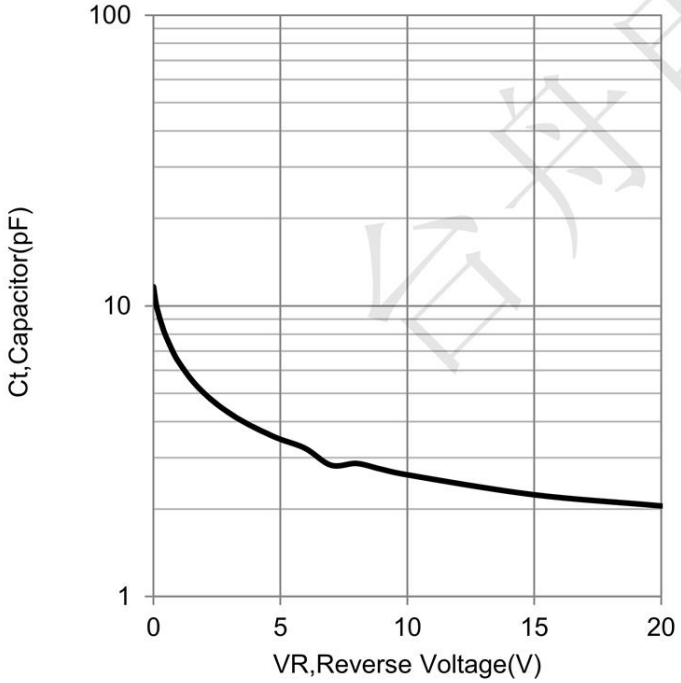
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



Forward Characteristics

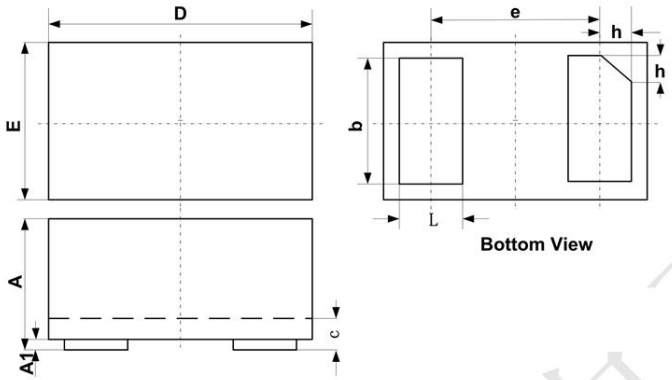


Reverse Characteristics



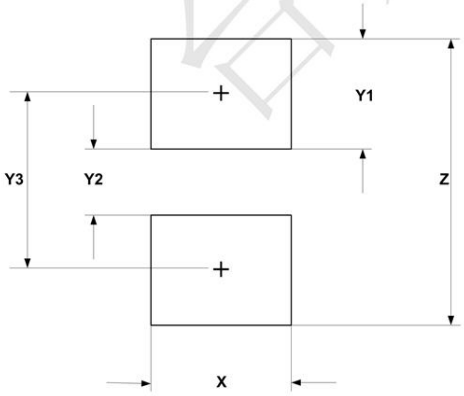
Capacitor Characteristics

DFN0603-2 Package Outline Drawing (0201)



SYM	DIMENSIONS		
	MILLIMETERS		
	MIN	NOM	MAX
A	0.230	0.300	0.330
A1	0.000	0.020	0.050
b	0.215	0.245	0.275
c	0.120	0.150	0.180
D	0.550	0.600	0.650
e	0.355 BSC		
E	0.250	0.300	0.350
L	0.160	0.190	0.220
h	0.079 BSC		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.30	0.012
Y1	0.25	0.010
Y2	0.15	0.006
Y3	0.40	0.016
Z	0.65	0.026